

Electrical Characteristics of IGBT @ Inverter $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ C$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	μA
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$I_C = 10mA, V_{CE} = V_{GE}$	5.0	6.5	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 10A, V_{GE} = 15V$	--	2.1	2.7	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	710	--	pF
C_{oes}	Output Capacitance		--	57	--	pF
C_{res}	Reverse Transfer Capacitance		--	12	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 10A,$ $R_G = 20\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	65	130	ns
t_r	Rise Time		--	65	130	ns
$t_{d(off)}$	Turn-Off Delay Time		--	80	160	ns
t_f	Fall Time		--	100	200	ns
E_{on}	Turn-On Switching Loss		--	0.15	--	mJ
E_{off}	Turn-Off Switching Loss		--	0.2	--	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 10A,$ $R_G = 20\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	70	140	ns
t_r	Rise Time		--	60	120	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	180	ns
t_f	Fall Time		--	200	350	ns
E_{on}	Turn-On Switching Loss		--	0.16	--	mJ
E_{off}	Turn-Off Switching Loss		--	0.3	--	mJ
T_{sc}	Short Circuit Withstand Time	$V_{CC} = 300V, V_{GE} = 15V$ @ $T_C = 100^\circ C$	10	--	--	μs
Q_g	Total Gate Charge	$V_{CE} = 300V, I_C = 10A,$ $V_{GE} = 15V$	--	35	50	nC
Q_{ge}	Gate-Emitter Charge		--	8	15	nC
Q_{gc}	Gate-Collector Charge		--	12	20	nC

Electrical Characteristics of DIODE @ Inverter T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
V _{FM}	Diode Forward Voltage	I _F = 10A	T _C = 25°C	--	1.9	2.8	V
			T _C = 100°C	--	2.0	--	
t _{rr}	Diode Reverse Recovery Time	I _F = 10A di / dt = 20 A/μs	T _C = 25°C	--	85	150	ns
			T _C = 100°C	--	110	--	
I _{rr}	Diode Peak Reverse Recovery Current		T _C = 25°C	--	0.7	1.4	A
			T _C = 100°C	--	1.0	--	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	--	30	105	nC
			T _C = 100°C	--	55	--	

Electrical Characteristics of DIODE @ Converter T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
V _{FM}	Diode Forward Voltage	I _F = 10A	T _C = 25°C	--	1.1	1.5	V
			T _C = 100°C	--	1.0	--	
I _R RM	Repetitive Reverse Current	V _R = V _{RRM}	T _C = 25°C	--	--	8	mA
			T _C = 100°C	--	5	--	

Thermal Characteristics

	Symbol	Parameter	Typ.	Max.	Units
Inverter	R _{θJC}	Junction-to-Case (IGBT Part, per 1/6 Module)	--	1.9	°C/W
	R _{θJC}	Junction-to-Case (DIODE Part, per 1/6 Module)	--	2.9	°C/W
Converter	R _{θJC}	Junction-to-Case (DIODE Part, per 1/6 Module)	--	2.5	°C/W
Weight		Weight of Module	60	--	g

NTC Thermistor Characteristics

	Symbol	Parameter	Tol.	Typ.	Units
Thermistor	R25	Rated Resistance @ T _C = 25°C	+/- 5 %	4.7	KΩ
	B(25/100)	B - Value	+/- 3 %	3530	